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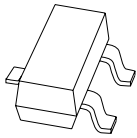
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Kind regards,

Team Nexperia



MMBD4148

High-speed switching diode

Rev. 01 — 4 June 2009

Product data sheet

1. Product profile

1.1 General description

High-speed switching diode, encapsulated in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- High switching speed: $t_{rr} \leq 4$ ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \leq 75$ V
- Low capacitance
- Reverse voltage: $V_R \leq 75$ V
- Small SMD plastic package

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_R	reverse voltage		-	-	75	V
I_R	reverse current	$V_R = 75$ V	-	-	0.5	μ A
t_{rr}	reverse recovery time		[1]	-	4	ns

[1] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected		
3	cathode		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
MMBD4148	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
MMBD4148	A6*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	75	V
V_R	reverse voltage		-	75	V
I_F	forward current		^[1] -	215	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 0.5 \mu\text{s}$; $\delta \leq 0.25$	-	500	mA
I_{FSM}	non-repetitive peak forward current	square wave	^[2]		
		$t_p = 1 \mu\text{s}$	-	4	A
		$t_p = 1 \text{ms}$	-	1	A
		$t_p = 1 \text{s}$	-	0.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C}$	^[1] -	250	mW
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	ambient temperature		-65	+150	$^\circ\text{C}$
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] $T_j = 25 \text{ }^\circ\text{C}$ prior to surge.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	330	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 7. Characteristics

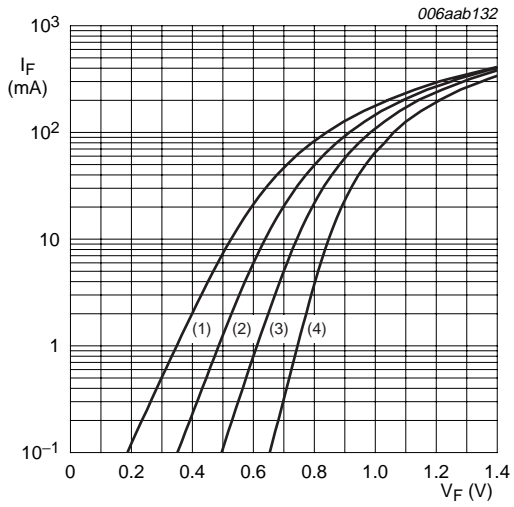
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage		[1]			
		$I_F = 1\text{ mA}$	-	-	715	mV
		$I_F = 10\text{ mA}$	-	-	855	mV
		$I_F = 50\text{ mA}$	-	-	1	V
		$I_F = 150\text{ mA}$	-	-	1.25	V
I_R	reverse current	$V_R = 25\text{ V}$	-	-	30	nA
		$V_R = 75\text{ V}$	-	-	0.5	μA
		$V_R = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	30	μA
		$V_R = 75\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0\text{ V}$	-	-	1.5	pF
t_{rr}	reverse recovery time		[2]	-	4	ns
V_{FR}	forward recovery voltage		[3]	-	1.75	V

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

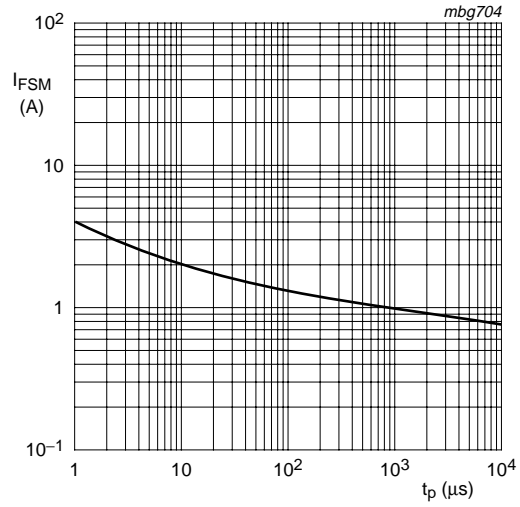
[2] When switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$.

[3] When switched from $I_F = 10\text{ mA}$; $t_r = 20\text{ ns}$.



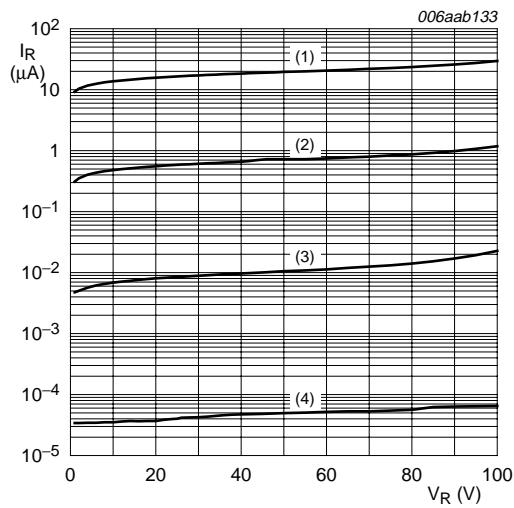
- (1) $T_{amb} = 150^\circ\text{C}$
- (2) $T_{amb} = 85^\circ\text{C}$
- (3) $T_{amb} = 25^\circ\text{C}$
- (4) $T_{amb} = -40^\circ\text{C}$

Fig 1. Forward current as a function of forward voltage; typical values



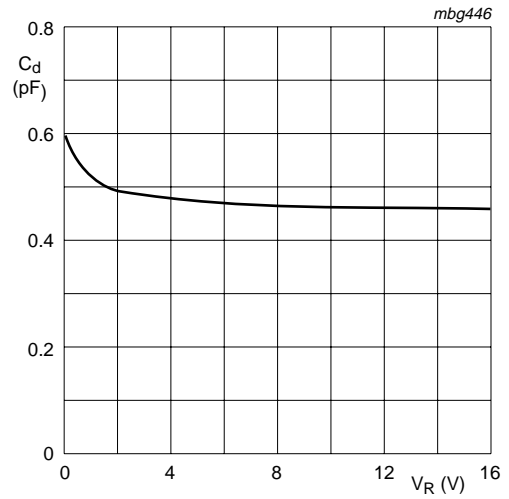
Based on square wave currents.
 $T_J = 25^\circ\text{C}$; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



- (1) $T_{amb} = 150^\circ\text{C}$
- (2) $T_{amb} = 85^\circ\text{C}$
- (3) $T_{amb} = 25^\circ\text{C}$
- (4) $T_{amb} = -40^\circ\text{C}$

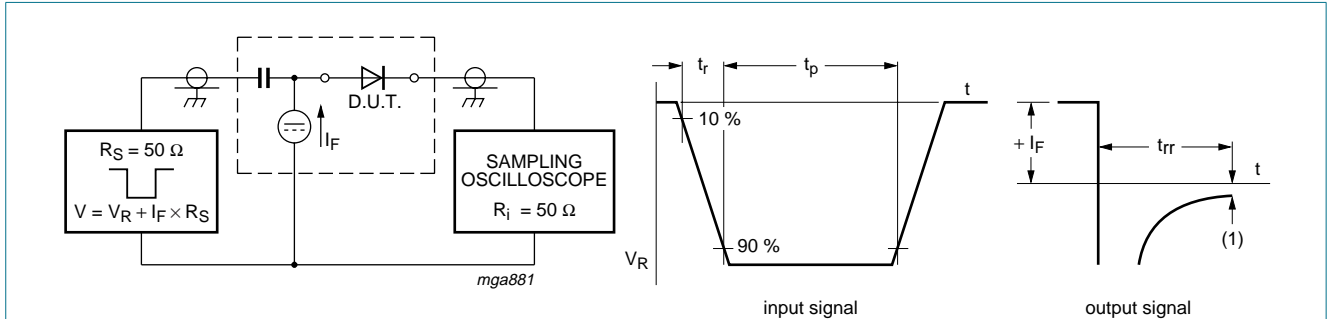
Fig 3. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}$; $T_{amb} = 25^\circ\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

8. Test information

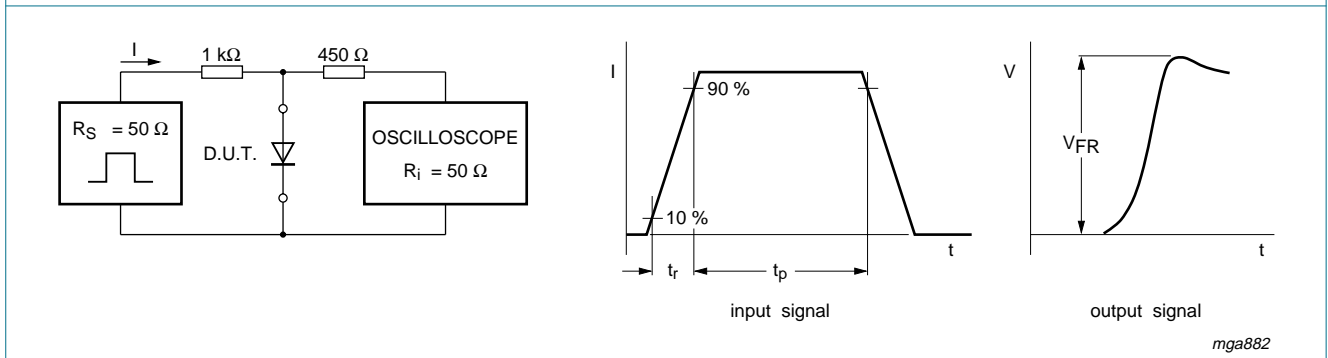


(1) $I_R = 1 \text{ mA}$

Input signal: reverse pulse rise time $t_r = 0.6 \text{ ns}$; reverse voltage pulse duration $t_p = 100 \text{ ns}$; duty cycle $\delta = 0.05$

Oscilloscope: rise time $t_r = 0.35 \text{ ns}$

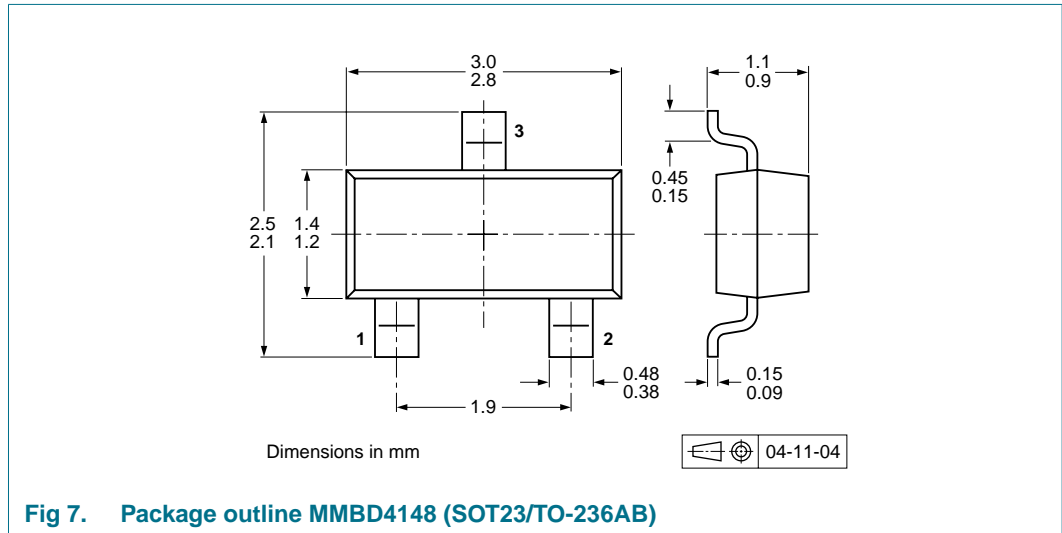
Fig 5. Reverse recovery time test circuit and waveforms



Input signal: forward pulse rise time $t_r = 20 \text{ ns}$; forward current pulse duration $t_p \geq 100 \text{ ns}$; duty cycle $\delta \leq 0.005$

Fig 6. Forward recovery voltage test circuit and waveforms

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
MMBD4148	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

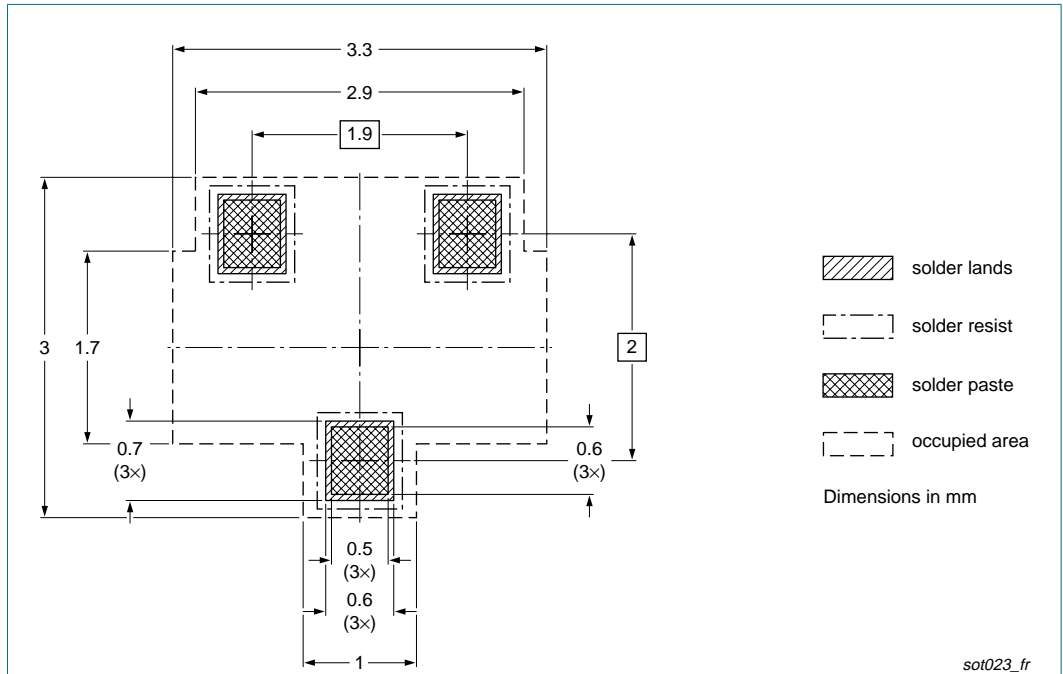


Fig 8. Reflow soldering footprint MMBD4148 (SOT23/TO-236AB)

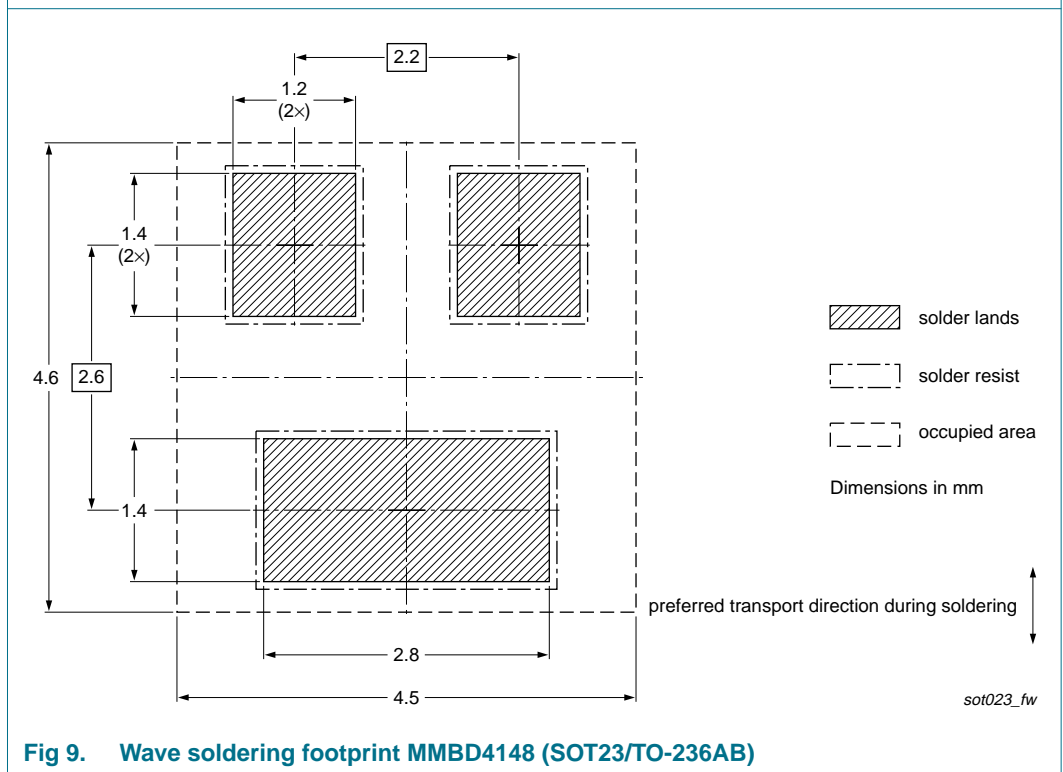


Fig 9. Wave soldering footprint MMBD4148 (SOT23/TO-236AB)

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
MMBD4148_1	20090604	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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